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2 **Supplementary Information for**

3 **Bulk vs Layer Confined RNiO_3 : Disentangling Lattice and Electronic Contributions to the** 4 **Metal-Insulator Transition**

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8 **This PDF file includes:**

9 Supplementary text

10 Figs. S1 to S11

11 References for SI reference citations

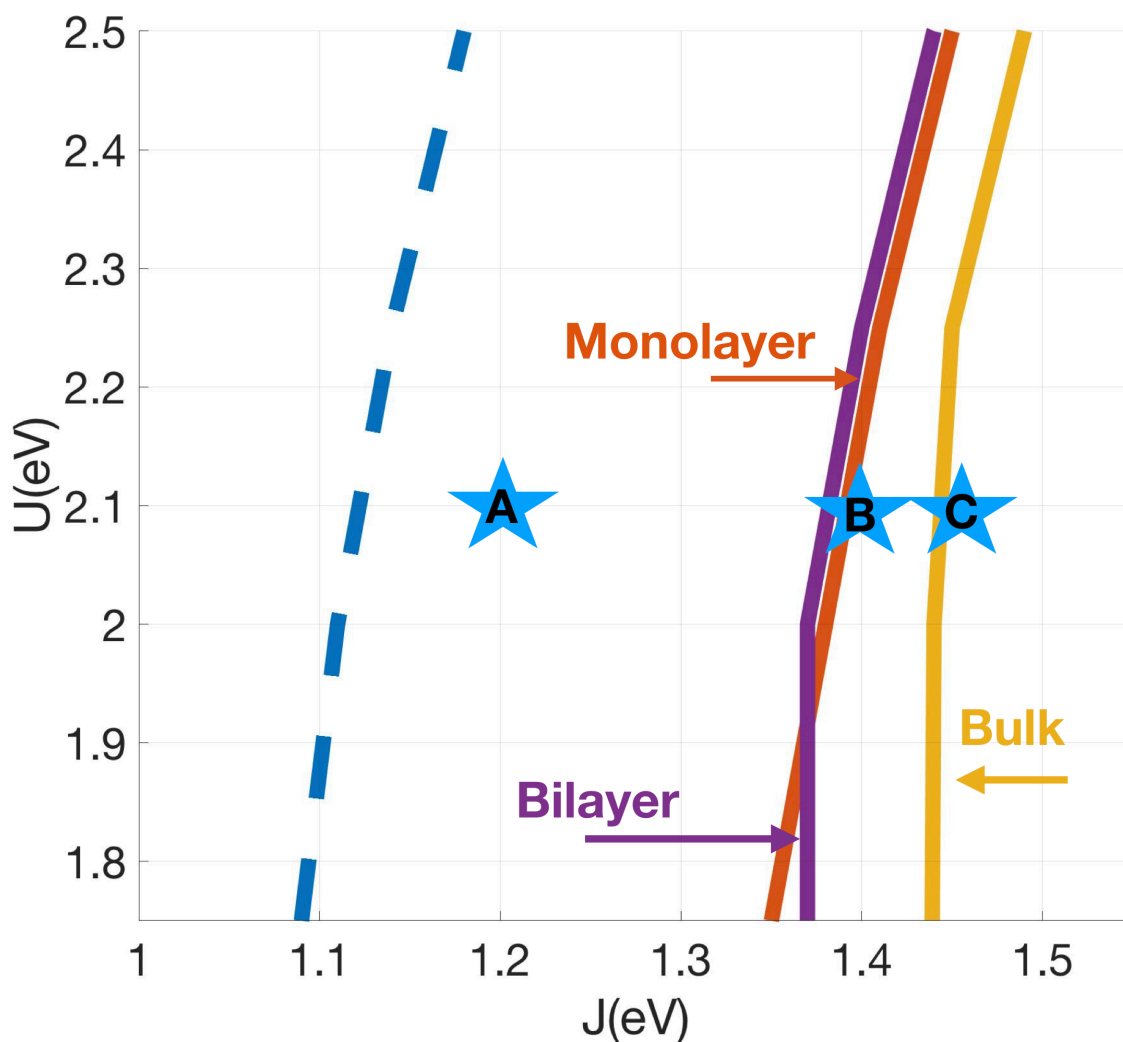


Fig. S1. Solid lines: boundaries of region of spontaneous electronic disproportionation and the associated metal-insulator transition in the (U, J) plane for DFT-relaxed bulk, bilayer and monolayer NNO in the absence of structural distortion. Insulating phases are to the right of the lines shown. The dotted line to the left shows the Metal-Insulator transition line for the bulk experimental Low T disproportionated structure calculated as in Ref (1). The phase diagram shows the same trend as the constructions in the main text, with the bulk less prone to electronic disproportionation than the heterostructures. The stars correspond to the points at which the constructions in the main text are plotted.

13 **Appendix A: DFT+DMFT Q=0 Phase Diagram.** In Figure S1 we plot the metal-insulator phase diagram calculated at $Q = 0$
14 for the different materials on the plane of interaction parameters U and J , i.e. determined by $E_{el}(\Delta N)$ exclusively. We
15 also plot a dashed line corresponding to the MIT transition for the experimental bulk low temperature, insulating structure,
16 calculated as in Ref. (1), to show the effect of the lattice distortion. We choose parameters U, J in the range in which the bulk
17 undisproportionated material is metallic. We note that the resulting J needed to obtain an insulating state is significantly
18 higher than in a more realistic calculation involving U, J and an inter-site Hartree term $V(2)$, however for simplicity and to
19 avoid overfitting multiple parameters we work within a U, J model as in previous work (1). Consistent with previous work
20 we find insulating solutions for values U, J that are to the right of $U-3J < 0$ (which corresponds to spontaneous electronic
21 disproportionation in the atomic limit), insulating solutions, in the absence of any structural disproportionation. The transitions
22 as a function of U and J are strongly first order. We find that spontaneous disproportionation ($\Delta N \neq 0$) is achieved for
23 a slightly smaller critical J for a given U in the monolayer and the bilayer than in the bulk. Despite minor differences in
24 bandwidth, the phase diagrams for the monolayer and bilayer are nearly identical.

25 Appendix B: DFT Technical Details

26 We use the Quantum Espresso (3) software package for our DFT calculations, Wannier90(4) to generate the extended Wannier
27 e_g orbitals, and the TRIQS software package(5) for the DMFT calculations with its various applications: DFTTools (6) for the
28 interface with Wannier90 and the CT-HYB DMFT solver(7) to solve the DMFT equations using the Hybridization expansion
29 impurity solver (8). We use ultrasoft pseudopotentials (9) and the PBE (10) version of the GGA exchange-correlation functional
30 formalism. To simulate the bulk material, we used a 20 atom $c(2 \times 2) \times 2$ unit cell, relaxed starting from the experimental structure;
31 for the $m=1$ superlattice we used 1 layer of NNO and 3 layers of NAO, while for $m=2$ we used 2 layers of each material,
32 making sure that the total number of layers is even in order to allow the octahedra to relax. For the bulk undisproportionated
33 calculation, we find that our high-temperature relaxed structure within GGA has a bandwidth that is only slightly smaller
34 than the experimental high temperature structure. In the phase diagram in figure 2, this leads to a small shift to the left in the
35 critical J for a given U of at most 0.05eV. Of the available functionals we have tried however (LDA, PBE and PBEsol), we find
36 that relaxations using GGA in the PBE formalism provide a bandwidth that is very close to the one using the experimental
37 high temperature structure as well as a phase diagram that is closer to the one obtained by using said structure. We also
38 find that the phase diagram difference between the undisproportionated structures is robust with respect to changing the
39 functional used in order to obtain the relaxed structures. For the initial DFT relaxations without structural disproportionation,
40 we found a k-point mesh of $5 \times 5 \times 4$ for the 20 atom bulk unit cell or $5 \times 5 \times 4$ for the heterostructures (equivalent to $7 \times 7 \times 8$ and
41 $7 \times 7 \times 12$) per formula unit are sufficient to generate quality structures. For consistency with the DFT+U results, we also
42 performed higher k-point calculations but found they do not affect results. For the various DFT+U relaxations involving
43 structural disproportionation, we impose ferromagnetic order. The k-point mesh has to be higher to differentiate between the
44 various possible local minima. Thus, for the 20 atom bulk is $7 \times 7 \times 5$, while for the 40 atom heterostructures it is $7 \times 7 \times 4$ (roughly
45 equivalent to a $10 \times 10 \times 10$ k-mesh per formula unit) in order to have a 1meV accuracy in the total energies of the relaxed
46 structures, however we have found that structures obtained using $5 \times 5 \times 2$ and $7 \times 7 \times 3$ k-point grids give nearly identical structural
47 results. For all calculations, the wavefunction energy cutoff is 35 Ry, and the density cutoff is 280Ry. A Marzari-Vanderbilt
48 smearing of 0.027 eV is used for the electron occupation function for all calculations. The energy convergence threshold for
49 relaxations is 10^{-9} eV and the force coverage threshold is $10^{-4} a.u.$, the electronic energy convergence threshold within the
50 electronic self-consistency loop is 10^{-12} eV.

51 To extract the tight-binding parameters for DMFT calculations, we obtain the antibonding e_g orbitals as a postprocessing
52 step using Wannier90 within the Maximally Localized Wannier Function framework.

53 **Appendix C: DFT+U Results and Technical Details.** One of the more difficult aspects of our calculations was obtaining structurally
54 disproportionated states for the heterostructures. While for the bulk material one can start from the experimental, low-
55 temperature insulating structure and perform a DFT+U, ferromagnetically ordered calculation, it is not trivial to obtain
56 structurally disproportionated solutions for the heterostructures. In order to obtain said solutions we first performed non-
57 magnetic, DFT calculations to obtain a starting, metallic, non-disproportionated solution. We then manually moved the Oxygen
58 atoms of the resulting NiO_6 octahedra closer or further away from the Ni atoms in an alternating way, and relaxed the structure
59 imposing a starting ferromagnetic electronic order and a $U=4$ eV. Following this relaxation we used the resulting structure as
60 an input to other relaxations with lower and larger U to obtain a set of structures with smoothly varying parameters. For very
61 small U ($U=0$ ev-1eV) it is more difficult to obtain structures that are part of a continuous set of structures, so we excluded the
62 structures at $U=1$ eV that are not part of the set.

63 For the DFT+U calculations, we performed calculations in the ferromagnetic phase, as our unit cells are not large enough
64 to reproduce the full experimentally determined magnetic structure in the bulk (with vector $q=(1/4, 1/4, 1/4)$) or bilayer
65 ($q=(1/4, 1/4, 0)$) while the magnetic structure in the monolayer is not known but with ferromagnetism and a $q=(1/4, 1/4, 0)$ vector
66 excluded. We use the FM state as a way to break symmetry leading to bond disproportionation and an alternating $S=1, S=0$
67 state, as more important in the physics of the final structure than the exact magnetic order. A Hund J is included implicitly
68 within spin-polarized DFT, however within the version of Quantum Espresso used for these calculations, only the effective
69 Dudarev $U_{eff} = (U - 2J)$ scheme is available, not allowing us to control U, J separately. For the two inequivalent Ni sites, as a
70 proxy for charge disproportionation, we use the difference in local magnetic moment. We find that the total magnetization
71 for the supercell is always equal to one Bohr magneton times the number of Nickel sites, as we would expect. However, the

72 projected magnetic moment on the Löwdin orbitals does not add up to this total magnetization, as the Löwdin orbitals are not
73 sufficient to describe the e_g valence states. However, making the assumption that the Löwdin magnetic moment is directly
74 proportional to the magnetic moment per site, we can then write $m_{Ni} \approx m_{Lowdin-total} * 2\mu_B / m_{total}$ where $m_{Lowdin-total}$ is
75 the total magnetization per pair of Ni sites: this is the ΔM .

76 Further supporting the picture of stronger electronic disproportionation in the heterostructures as a driving mechanism, we
77 present results for the bulk, bilayer and monolayer structures as obtained by DFT+U using spin-polarized calculations in the
78 FM state and full relaxations in Figure S2. We find that, for small U (U=0eV,1eV), the heterostructures have a critical U
79 under which the lattice stiffness is too strong to allow disproportionation, and even when it is allowed, there is a competition
80 between the disproportionated state and a Jahn-Teller distorted state with lower disproportionation. As expected, the critical
81 U at which the monolayer disproportionates is higher than for the bilayer which is higher than for the bulk. Consistent
82 with the DFT+DMFT results, however, once electronic disproportionation is allowed the monolayer is more electronically
83 disproportionated than the bulk. Q are very similar for all three structures, with the exception of large U for which both the
84 bulk and bilayer structural disproportionation stop increasing, while the monolayer disproportionation increases past that of
85 both.

86 We also present structural information on the structures obtained for various U within DFT+U and note which structures
87 were excluded from our fit for the various parameters in Figures S3, S4 and S5

Appendix D: DFT+DMFT Technical Details. The Slater-Kanamori Hamiltonian solved by DMFT using the tight binding model extracted from the Wannier functions has the form on each lattice site:

$$\hat{H}_U = U \sum_m \hat{n}_{m\uparrow} \hat{n}_{m\downarrow} + (U - 2J) \sum_{m \neq m'} \hat{n}_{m\uparrow} \hat{n}_{m'\downarrow} + (U - 3J) \sum_{m < m', \sigma} \hat{n}_{m\sigma} \hat{n}_{m'\sigma} - J \sum_{m \neq m'} c_{m\uparrow}^\dagger c_{m\downarrow} c_{m'\downarrow}^\dagger c_{m'\uparrow} + J \sum_{m \neq m'} c_{m\uparrow}^\dagger c_{m\downarrow}^\dagger c_{m'\downarrow} c_{m'\uparrow} \quad [1]$$

88 In the DFTTools interface between DFT and DMFT we use a k-mesh of 14x14x14 for the bulk material, and a k-mesh of
 89 12x12x6 for the heterostructure to obtain quality local density of states. The DMFT calculations in this paper are performed
 90 in a single-shot formalism, i.e. the new density is not updated into the DFT loop. Most DMFT calculations in this paper,
 91 unless mentioned otherwise, are done at an inverse temperature $\beta = 40eV^{-1}$, equivalent to a temperature of 290K. Most
 92 DMFT calculations are run for 15 steps using 10^7 QMC cycles. Calculations that require higher precision are ran for 35
 93 steps, the first 30 using around 10^7 QMC cycles, and the final 5 using 3×10^8 cycles. To compare with previous literature,
 94 we've also performed density-density only calculations to benchmark our calculations. We find that using the Slater-Kanamori
 95 Hamiltonian shifts the metal-insulator phase boundary to slightly higher values of J given a particular U ($\approx 0.2eV$).

96 **Appendix E: Model Parameter Extraction.** In order to extract the relevant parameters we need, we use the structures generated
 97 within DFT+U, carefully selecting them such that a smooth variation of the structural parameters is obtained as described in
 98 Appendix D. We need to extract the following: $g^{DFT} = \frac{\partial \Delta_S}{\partial Q}$, $\chi_0 = \frac{\partial \Delta_N}{\partial \Delta_S}$, $\lambda = g^{DFT} \chi_0$ and finally the stiffness k, which can
 99 then be extracted by doing DFT calculations on said structures. We then get: $E_{DFT}(Q) = (\frac{k}{2} - \frac{1}{4}(g^{DFT})^2 \chi_0) Q^2 = \frac{c}{2} Q^2$ with c,
 100 g, χ_0 constants we extract from the structures we generated as a function of Q. Our results are shown in Figures: S6, S7, S8 and
 101 S9. In order to benchmark this method as compared to explicitly imposing a Q, we compared our results on the bulk material
 102 with previous work (11) in which multiple structures were generated by modulating the bond disproportionation Q alone, and
 103 find that our results are consistent. We also note that while using bulk structures obtained through GGA relaxation does lead
 104 to slightly lower bandwidths than those obtained using the experimental structure, this only affects the results by shifting all
 105 the phase diagrams to lower J for a given U by about $0.05eV$ as compared to the experimental structure. As the stiffness k
 106 and the static response functions $g^{DFT} = \frac{\partial \Delta_S^{DFT}}{\partial Q}$ and $\chi_0 = \frac{\partial \Delta_N^{DFT}}{\partial \Delta_S^{DFT}}$ do not depend on the bandwidth by more than a fraction
 107 of a percent within our calculations, and the bond angles of the disproportionated structures remains the same up to within
 108 < 1 degree within our relaxed spin-polarized calculations, we can simulate a large number of disproportionated structures
 109 with varying Q and assuming that the DFT Hamiltonian would look like the one corresponding to the undisproportionated,
 110 nonmagnetic structure plus an on-site energy difference $\Delta_S^{DFT} = g^{DFT} Q$. The spin-polarized relaxed structures have bond
 111 angles that are slightly more bent than those in the non-magnetic calculations, however as was shown in (11), neither k nor g
 112 depend on the bandwidth; we do expect a slightly larger χ_0 in the structures obtained using spin-polarized DFT+U by about
 113 3-5% due to the slightly reduced bandwidth.

114 **Appendix F: Experimental Hole Determination.** Experimental values of the Ni eg hole ratio were extracted from x-ray linear
 115 dichroism (XLD) measurements on NNO/NAO superlattices, which can be directly compared to theory. The sample growth
 116 and measurement procedures are described in Ref. (12). To extract r experimentally, the XLD sum rule (13) is applied for the
 117 Ni L edge, $r = \frac{3I_{3z^2-r^2}}{4I_{x^2-y^2} - I_{3z^2-r^2}}$, where I_p corresponds to the integrated absorption measured with the polarization parallel to p.
 118 Figure S10 shows the absorption for in-plane and out-of-plane polarizations as well as the difference spectrum of the monolayer
 119 NNO/NAO superlattice. The values of r for the monolayer NNO/NAO superlattice, bilayer NNO/NAO superlattice, and bulk
 120 NNO samples are 0.91 ± 0.03 , 1.00 ± 0.02 , and 1.02 ± 0.02 , respectively.

121 **Appendix G: DFT+U Structures.** One of the most difficult aspects of our calculation consisted in obtaining disproportionated
 122 structures for the heterostructures using DFT+U. To best serve future research in this direction, we present the lattice vectors
 123 and atomic coordinates obtained within DFT+U for the bulk, $(\text{NNO})_2/(\text{NAO})_2$ and $(\text{NNO})_1/(\text{NAO})_3$ structures for $U=4$ using
 124 PBE as the exchange correlation potential and ultrasoft pseudopotentials. To obtain undisproportionated ($Q=0$) structures,
 125 one can use these structures as input for a DFT calculation without U and without magnetism. To obtain structures with
 126 varying amounts of disproportionation Q as in Appendix E, one can perform calculations with Ferromagnetic order with slowly
 127 increasing/decreasing U in order to obtain structures with varying Q but similar Jahn-Teller distortion. The in-plane lattice
 128 constant of the heterostructures is fixed to the DFT values of the in-plane lattice constant of NNO in order to avoid issues
 129 related to the separate relaxation of the unit cell of NAO.

130 **Estimation of Q and Relative Oxygen Displacements** Each octahedron has two inequivalent bond lengths in the xy
 131 plane; the bond lengths along z are equivalent for the monolayer and the bulk but not for the bilayer. To obtain Q, we take
 132 differences of pairs of bond lengths corresponding to the two inequivalent octahedra as follows: we pick the longer in-plane
 133 Ni-O bonds for each and take the difference between the large and small octahedron, then the difference between the shorter
 134 in-plane Ni-O bonds, and finally the equivalent out-of-plane Ni-O bonds. We then have Q as mentioned in the main text:

$$Q = \sqrt{\frac{\sum_i (l_{LB}^{(i)} - l_{SB}^{(i)})^2}{6}} \quad [2]$$

136 where $l^{(i)}$ are the lengths of the Ni-O bonds. In order to estimate the relative oxygen displacements along the Ni-Ni lines
 137 as shown in Figure 2 in a consistent manner (avoiding issues related to the Jahn-Teller distortions) we had to use certain
 138 approximations. Namely, for the in-plane average displacement, we take the difference between the average in-plane bond
 139 length of each octahedra and multiply it by $\cos(\bar{\angle}_{O-Ni-Ni})$, where $\bar{\angle}_{O-Ni-Ni}$ corresponds to averaging over the O-Ni-Ni
 140 bond angle. For the out-of-plane displacement of the oxygen atoms along the Ni-Ni direction, we perform the same
 141 calculation but without averaging over bond angles. We note that this gives the same result as calculating the displacement
 142 along z. For the Ni-O-Al displacement, as the interfacial disproportionation mode involves additional complications (relative
 143 displacements along z of the two Al atoms and a slight displacement along x-y relative to the Ni atoms), we take the relative
 144 displacement of the atoms along z instead as the Al atoms are slightly displaced along z relative to each other and along the xy
 145 plane relative to Ni.

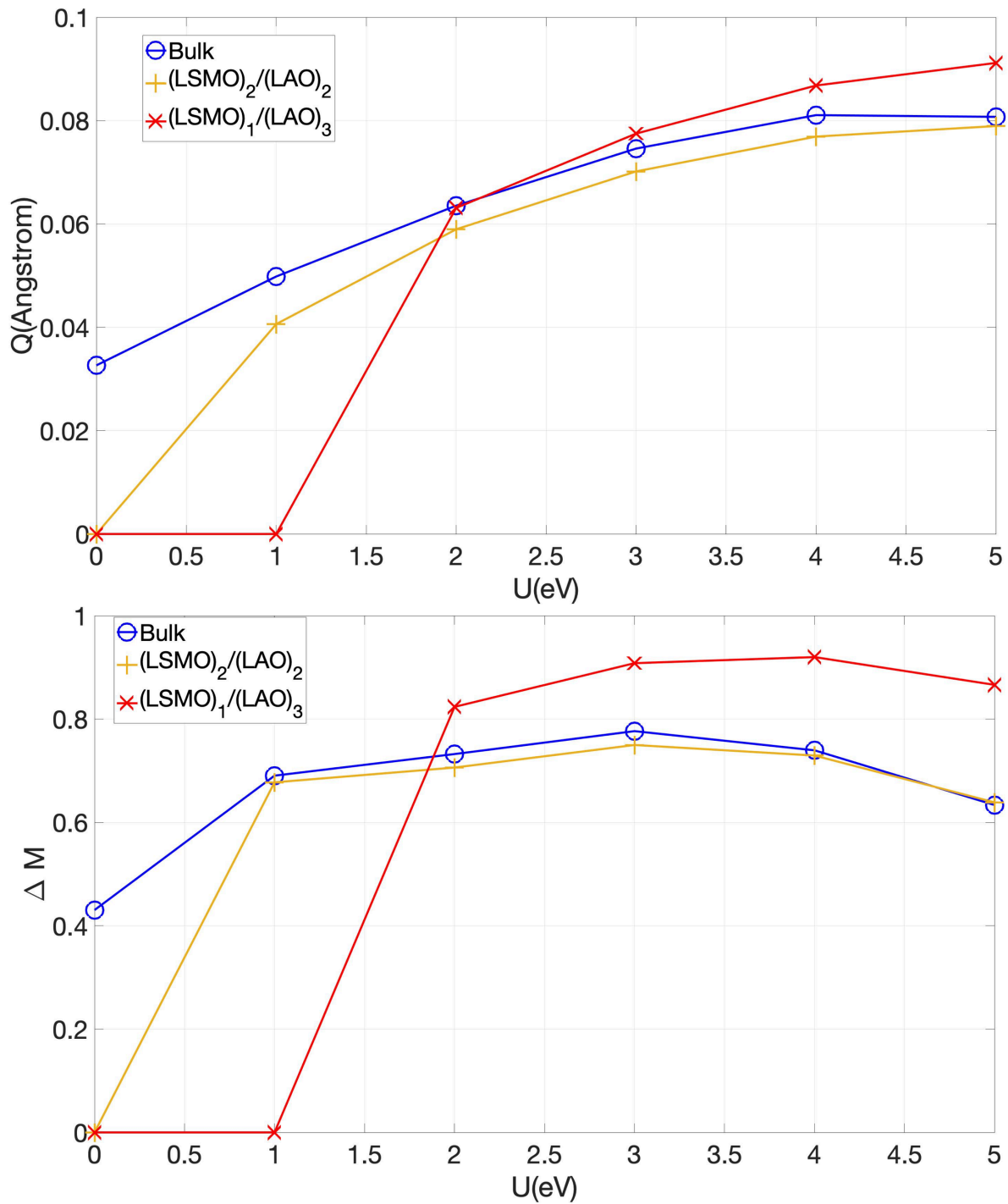


Fig. S2. Electronic and structural disproportionation within DFT+U for the various relaxed structures. For small $U=0\text{eV}$ for all structures as well as for $U=1\text{eV}$ for the heterostructures we picked the local minimum corresponding to a similar symmetry as for the higher U .

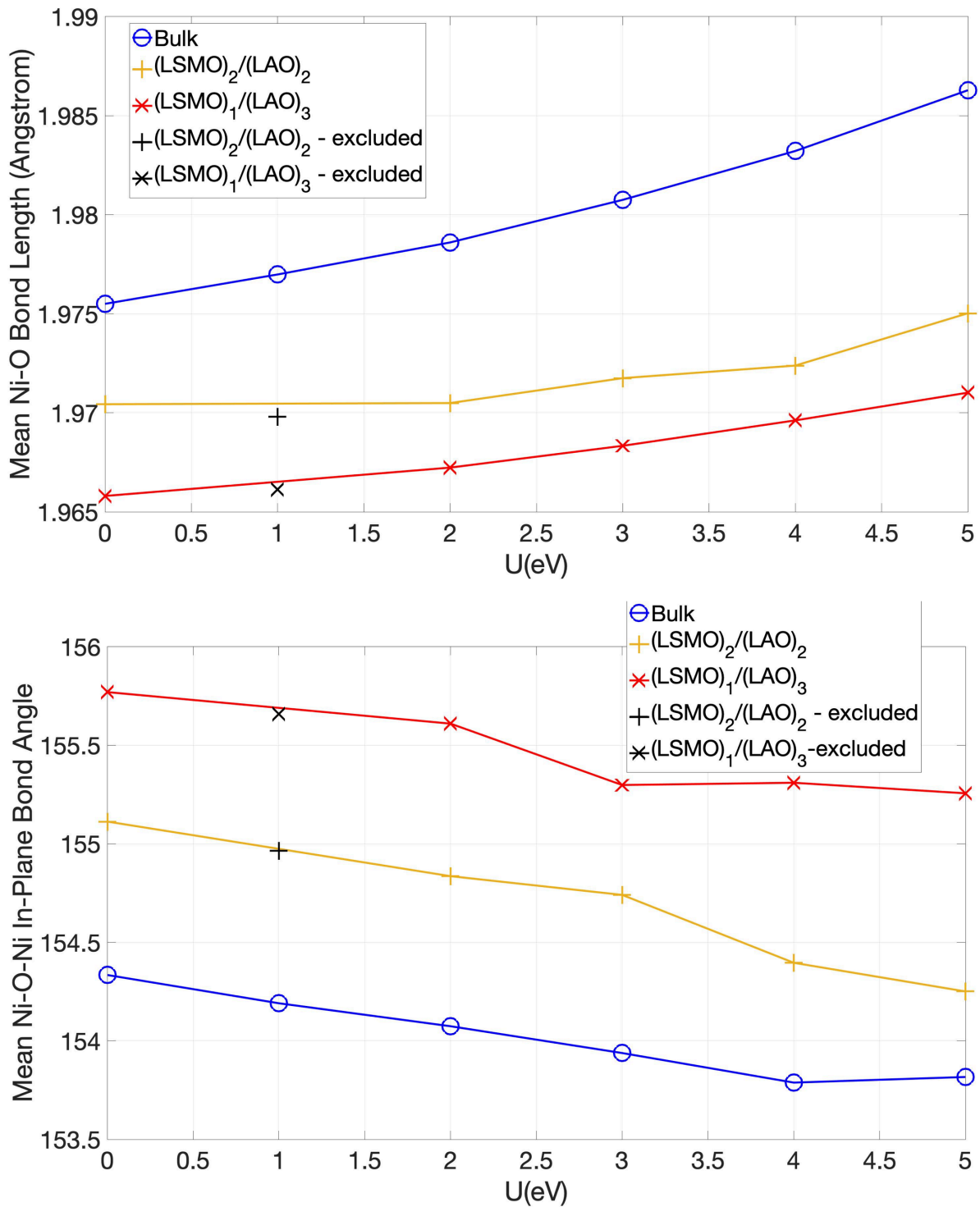


Fig. S3. Mean Ni-O bond lengths and mean in plane Ni-O-Ni bond angles for the structures used to obtain the parameters for our model as a function of the U used to generate the heterostructures. For U=0eV we picked the local minimum corresponding to the same symmetry as for the higher U. For the heterostructures at U=1eV we did not obtain a structure that continuously fits among the others and did not use it for the fit. We include all points for reference.

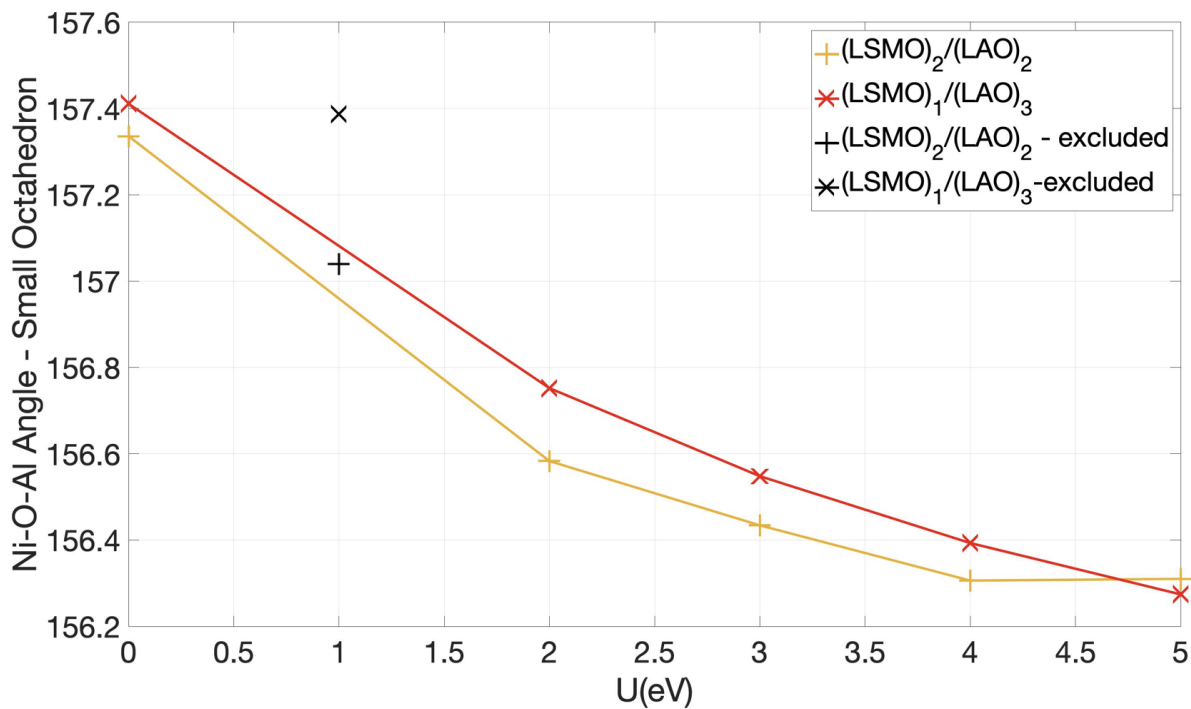
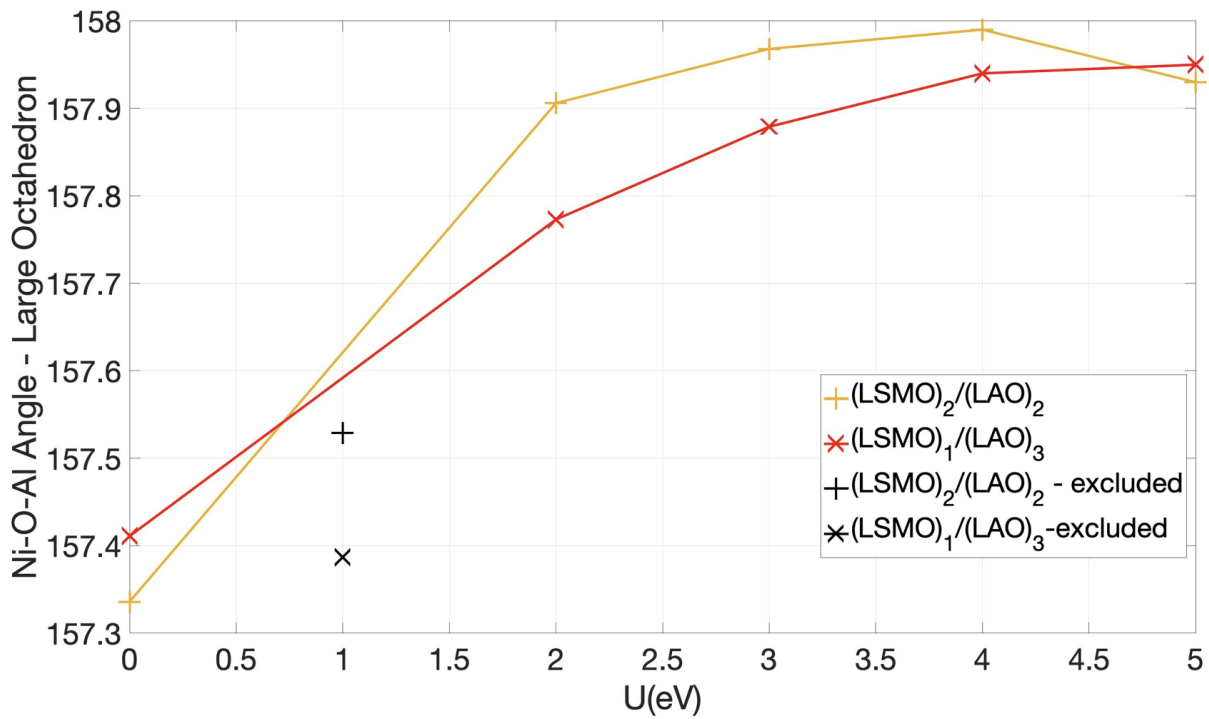


Fig. S4. Ni-O-Al bond angles for the large and small NiO₆ octahedra. The bond angles corresponding to the larger octahedra are straighter. Plot is as a function of the U used to generate the structures within DFT+U. For U=0eV we picked the local minimum corresponding to the same symmetry as for the higher U. At U=1eV we could not obtain a structure that continuously fits among the others and did not use it. We include the resulting points for reference.

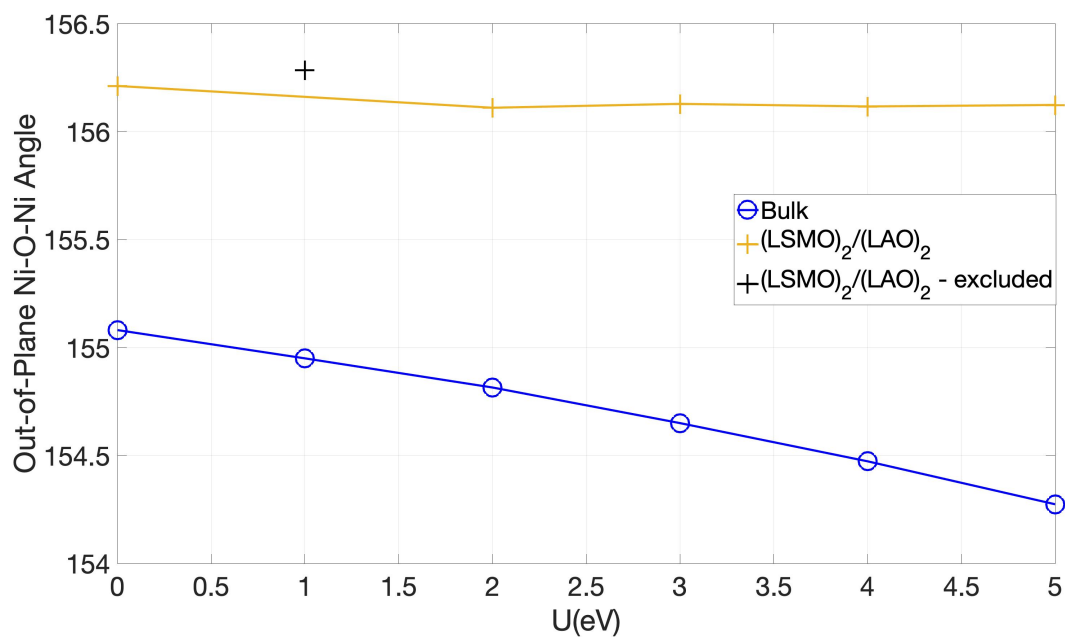


Fig. S5. Ni-O-Ni out of plane angles. Plot is as a function of the U used to generate the structures within DFT+U. For U=0eV we picked the local minimum corresponding to the same symmetry as for the higher U. At U=1eV for the bilayer we could not obtain a structure that continuously fits among the others and did not use it. We include the resulting points for reference.

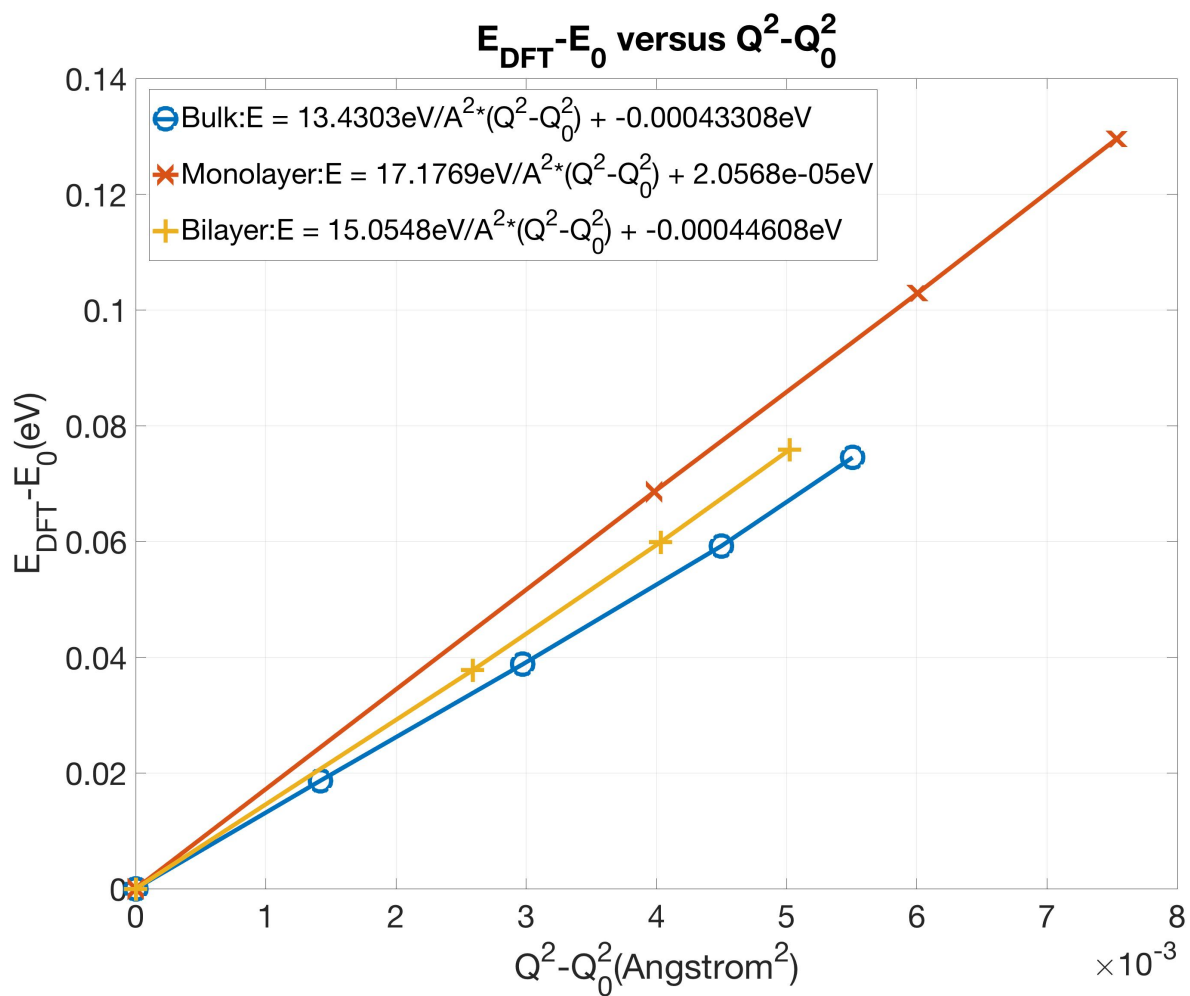


Fig. S6. Plot of energy per 2 formula units of NNO for the different structures for different Q , using structures obtained from DFT+U calculations. The energy and Q^2 are plotted relative to the energy of the smallest Q that are included in the plot.

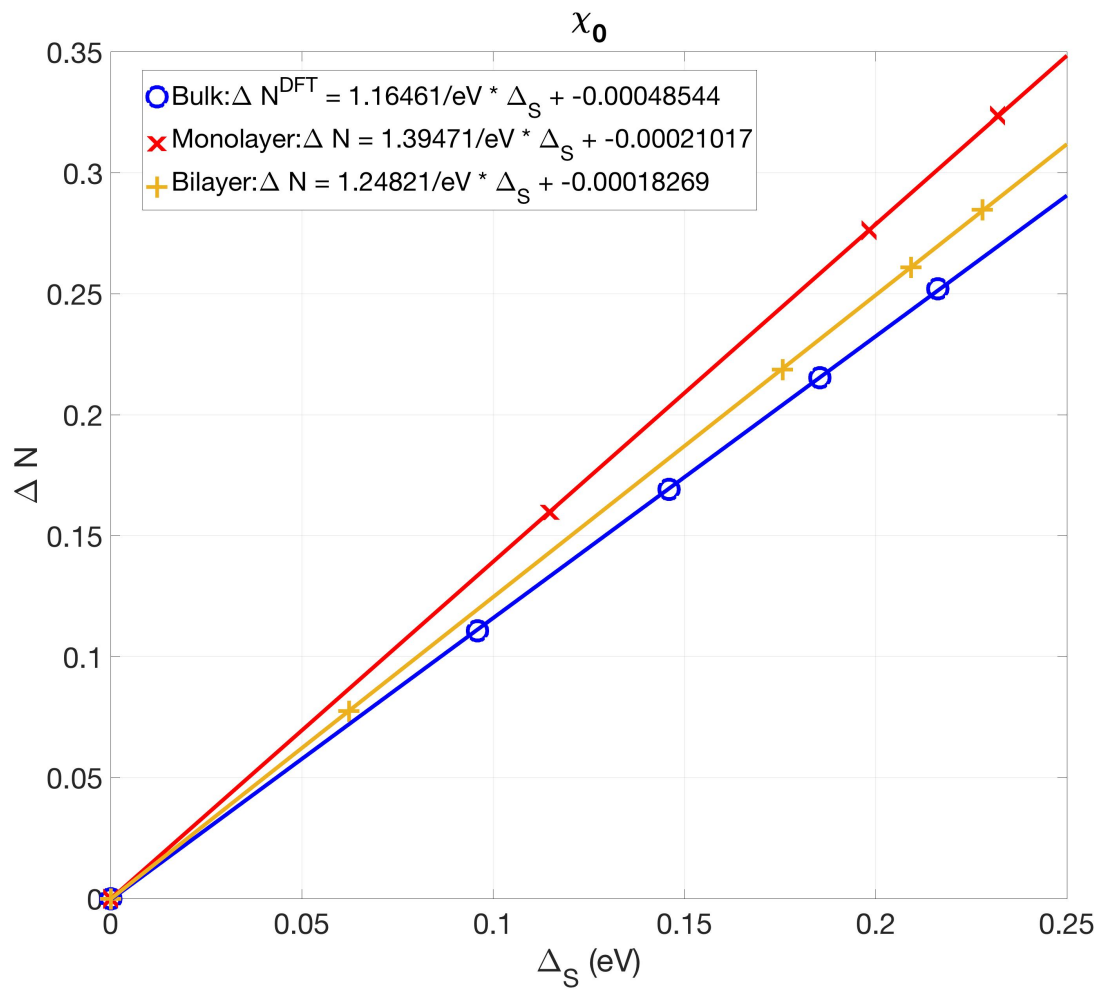


Fig. S7. Fit to obtain the static electronic response for the three materials, χ_0

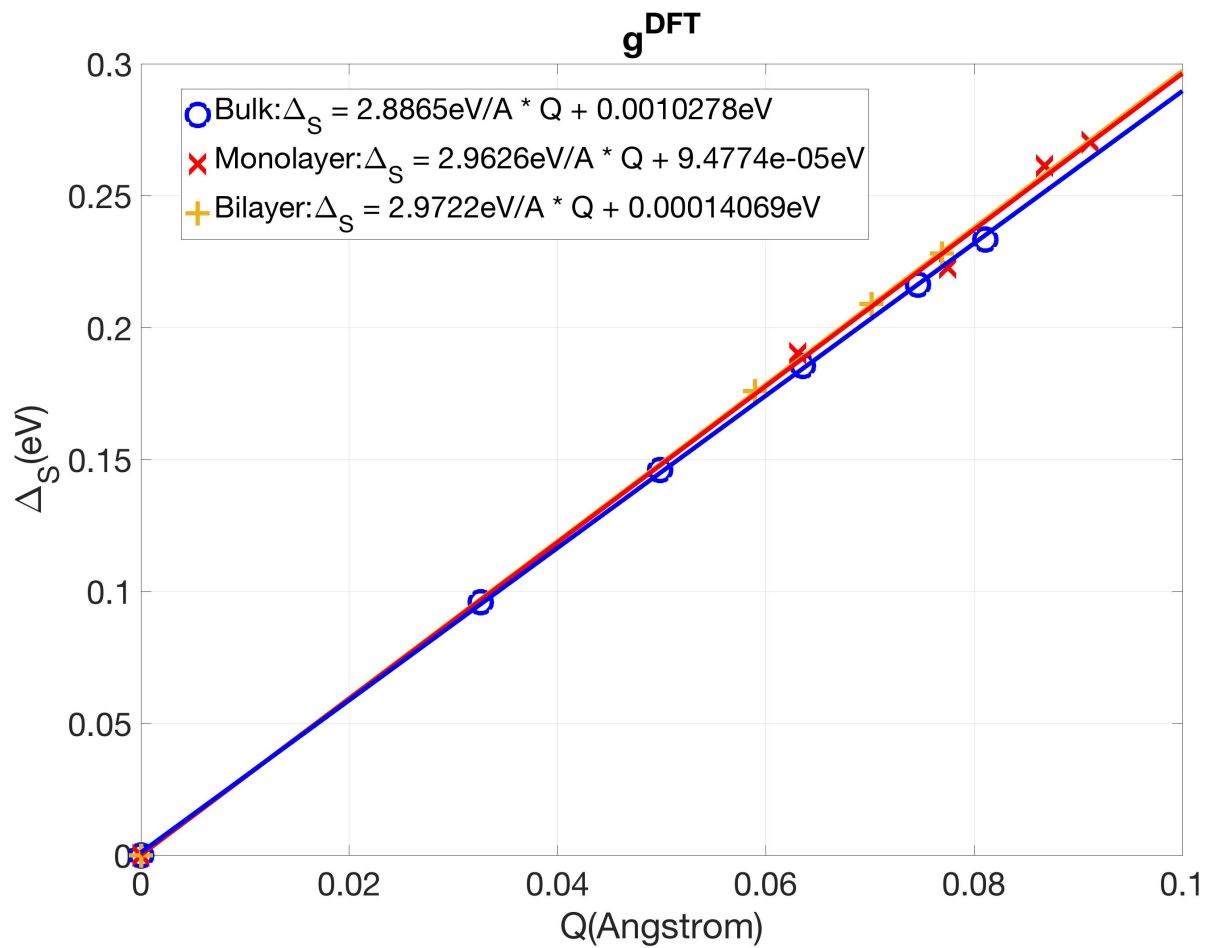


Fig. S8. Fit to obtain the linear coupling coefficient within DFT, g^{DFT}

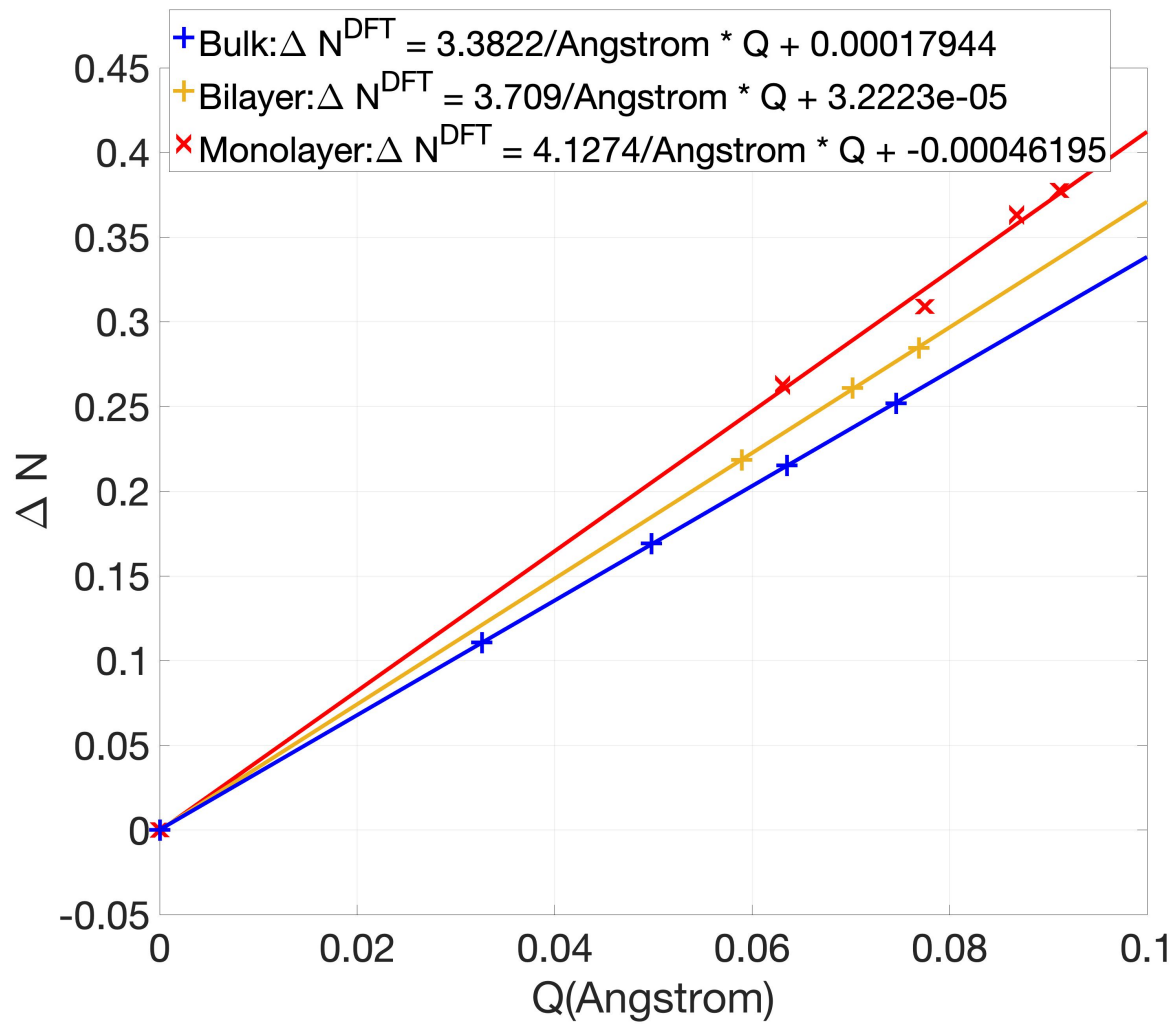


Fig. S9. ΔN^{DFT} versus Q as extracted from DFT; $\frac{\Delta N}{Q} = \lambda^{DFT} = g^{DFT} \chi_0$ as obtained from this fit compares well with the results from multiplying the previously obtained $g^{DFT} \chi_0$

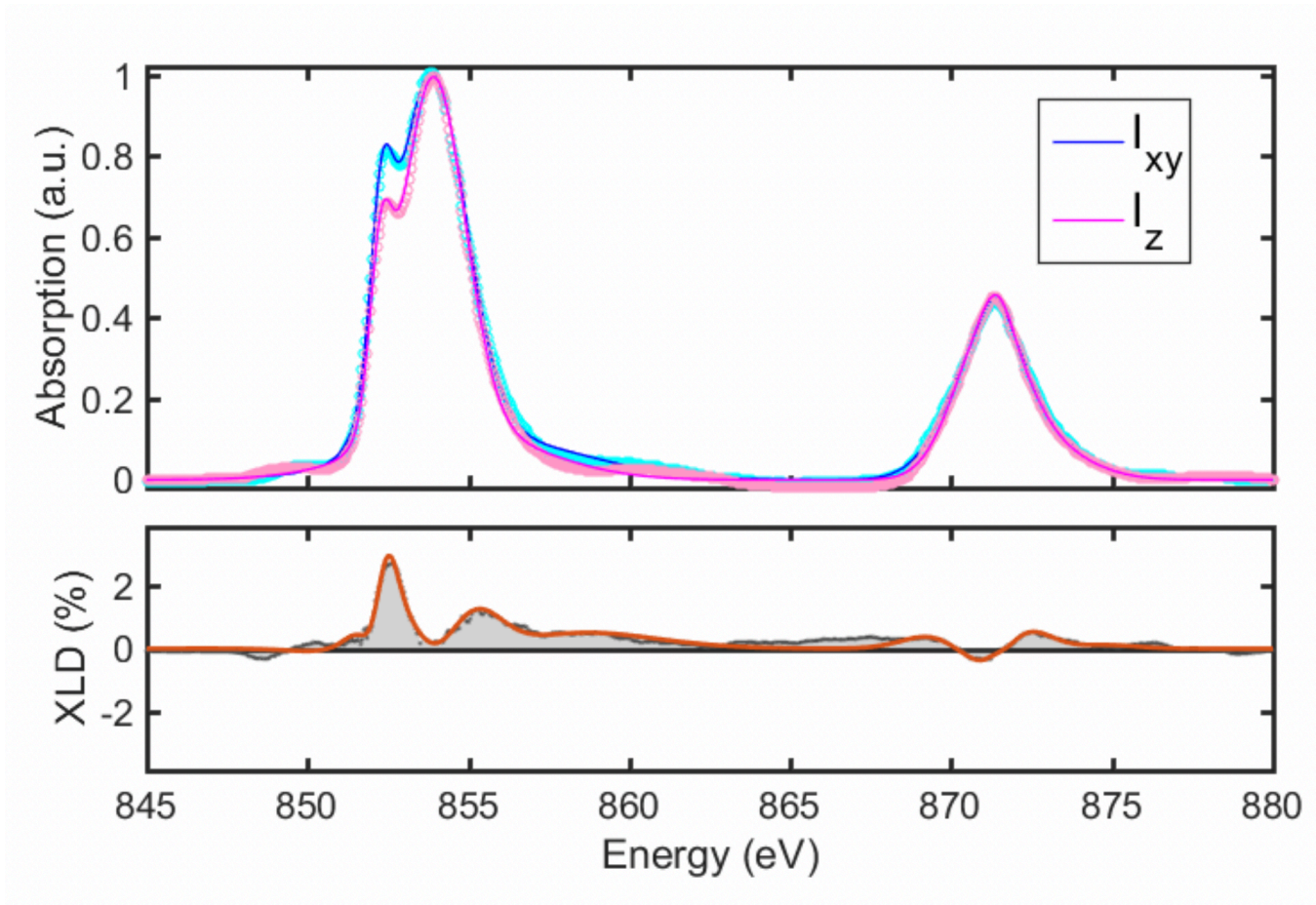


Fig. S10. (top) X-ray absorption spectra and (bottom) x-ray linear dichroism of monolayer NNO/NAO superlattice. Blue and pink curves in top panel correspond to absorption with polarization in-plane and out-of-plane, respectively.

(NNO)₁/(NAO)₃

Cell Parameters (in Angstrom):

v1=(5.409, 0.0, 0.0)

v2=(0.0, 5.4611, 0.0)

v3=(0.0, 0.0, 15.175280)

Atomic positions (in crystal coordinates):

Al	0.002291200	0.504226268	0.870278522
Al	0.499365893	0.004510625	0.871532046
O	0.272860482	0.279302045	0.888698314
O	0.773709122	0.231657323	0.854909303
O	0.224525821	0.777699894	0.888404474
O	0.729333362	0.728528955	0.854353892
Nd	-0.004972271	-0.023052494	0.747584510
Nd	0.507235555	0.476933097	0.747419071
O	0.064305399	0.509316644	0.747045799
O	0.438756953	0.009983690	0.747854337
Al	0.001090974	0.498002330	0.623338698
Al	0.501095952	-0.001998455	0.623342159
O	0.267806573	0.264662436	0.606676326
O	0.767541455	0.230816295	0.639861802
O	0.234632427	0.765210494	0.606820881
O	0.734374530	0.731356814	0.640002390
Nd	0.007165467	0.019092677	0.499077428
Nd	0.494936041	0.519118225	0.499234985
O	-0.062103468	0.486713918	0.499618681
O	0.563415880	-0.013967416	0.498815709
Al	-0.000113376	0.491832442	0.376357309
Al	0.502826771	-0.008443170	0.375118034
O	0.272846493	0.267513534	0.392296392
O	0.777654542	0.218342335	0.358257758
O	0.228474912	0.764388246	0.391739703
O	0.729306855	0.716740686	0.357966131
Nd	-0.002865895	-0.041861737	0.248534583
Nd	0.512079113	0.455946706	0.248640397
O	0.073676124	0.506938202	0.248813517
O	0.434338692	0.007096125	0.253172304
Ni	0.001080198	0.498058289	0.123307519
Ni	0.501087166	-0.001965303	0.123310511
O	0.280551672	0.290699118	0.102781221
O	0.206911829	0.779326018	0.102977656
O	0.795245358	0.216799581	0.143667880
O	0.721635647	0.705427054	0.143865883
Nd	0.005040367	0.037946435	-0.001889267
Nd	0.490083803	0.540133267	-0.002001036
O	-0.071531151	0.489149511	-0.002178785
O	0.567826734	-0.011021368	-0.006534040

(NNO)₂/(NAO)₂

Cell Parameters (in Angstrom):

v1=(5.409, 0.0, 0.0)

v2=(0.0, 5.4611, 0.0)

v3=(0.0, 0.0, 15.288983)

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Al	0.002354058	0.507015921	0.871525770
Al	0.499916979	0.006858316	0.870690215
O	0.275415606	0.278821961	0.888677035
O	0.771640150	0.233407070	0.854447461
O	0.229802143	0.780067435	0.888692268
O	0.729509987	0.735484094	0.854758027
Nd	-0.006056450	-0.019276186	0.748142290
Nd	0.507206098	0.480722892	0.748499805
O	0.064015077	0.515509833	0.748811664
O	0.437133626	0.015514756	0.747836103
Al	0.001247649	0.506854806	0.625951477
Al	0.498801669	0.007011886	0.625121740
O	0.271369183	0.280077131	0.607965285
O	0.771654506	0.235470427	0.641870908
O	0.225728263	0.778832092	0.607981764
O	0.729501557	0.733389299	0.642185188
Nd	0.005419270	0.038437488	0.499427789
Nd	0.490137400	0.539614944	0.499663738
O	-0.072537841	0.488615537	0.500667844
O	0.567965132	-0.010145273	0.503477953
Ni	0.000413083	0.495084380	0.374942243
Ni	0.501681588	-0.005269661	0.375061871
O	0.282716972	0.288026372	0.395152629
O	0.796011931	0.209908246	0.353879001
O	0.206699657	0.778880710	0.395008325
O	0.716917277	0.700410390	0.353765243
Nd	-0.010195242	-0.053963199	0.248217546
Nd	0.511410483	0.446035929	0.248430179
O	0.075098545	0.503873635	0.251539015
O	0.426133591	0.003859997	0.245135490
Ni	-0.000487426	0.494725501	0.121615235
Ni	0.500783686	-0.004916256	0.121721417
O	0.294522169	0.278915625	0.101680597
O	0.218434375	0.788070787	0.101534093
O	0.784310194	0.200375998	0.142873773
O	0.705159603	0.709876499	0.142754624
Nd	0.011037976	0.039629123	-0.003007638
Nd	0.495745808	0.538451129	-0.002775951
O	-0.066792587	0.489865558	-0.006827409
O	0.573697455	-0.011376090	-0.004021607

(NNO)-bulk

Cell Parameters (in Angstrom):

v1=(5.421605612 0.000000000 -0.000867789)

v2=(0.000000000 5.534560397 0.000000000)

v3=(-0.009805518 0.000000000 7.694108641)

Atomic positions (in crystal coordinates):

Nd	0.988403755	0.052409150	0.249942861
Nd	0.011596245	0.947590850	0.750057139
Nd	0.511596245	0.552409150	0.250057139
Nd	0.488403755	0.447590850	0.749942861
Ni	0.500000000	0.000000000	0.000000000
Ni	-0.000000000	0.500000000	0.500000000
Ni	0.500000000	0.000000000	0.500000000
Ni	-0.000000000	0.500000000	0.000000000
O	0.078881709	0.485104567	0.255315024
O	0.921118291	0.514895433	0.744684976
O	0.421118291	0.985104567	0.244684976
O	0.578881709	0.014895433	0.755315024
O	0.703751849	0.284852430	0.042686134
O	0.296248151	0.715147570	0.957313866
O	0.796248151	0.784852430	0.457313866
O	0.203751849	0.215147570	0.542686134
O	0.215032827	0.204772812	0.958220497
O	0.784967173	0.795227188	0.041779503
O	0.284967173	0.704772812	0.541779503
O	0.715032827	0.295227188	0.458220497

Fig. S11. Crystal lattice vectors and atomic coordinates in crystal units for relaxed structures obtained via DFT+U with a U=4eV.

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